

N-Channel JFET

40 V, 55 to 95 μ A, 0.10 ms, CP

2SK545



SC-59 / CP3
CASE 318BJ

Features

- Small I_{GSS}
- Small C_{iss}
- Ultrasmall Package permitting 2SK545–applied Sets to be Compact
- This is a Pb–Free Device

Applications

- Impedance Converter Applications
- Infrared Sensor

ABSOLUTE MAXIMUM RATINGS (at $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Drain–to–Source Voltage	V_{DSS}	40	V
Gate–to–Drain Voltage	V_{GDS}	–40	V
Gate Current	I_G	10	mA
Drain Current	I_D	1	mA
Allowable Power Dissipation	P_D	100	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_{STG}	–55 to +125	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MARKING DIAGRAM

B11 = Specific Device Code

ELECTRICAL CONNECTION

ORDERING INFORMATION

Device	Package	Shipping [†]
2SK545–11D–TB–E	SC–59/CP3 (Pb–Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications,

2SK545

Table 1. ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Gate-to-Drain Breakdown Voltage	$V_{(BR)GDS}$	$I_D = -10 \mu\text{A}, V_{DS} = 0 \text{ V}$	-40			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				

TYPICAL CHARACTERISTICS

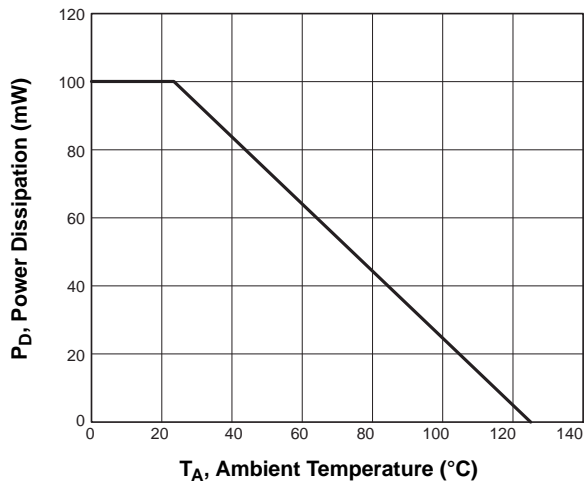


Figure 5. Power Dissipation vs. Ambient Temperature

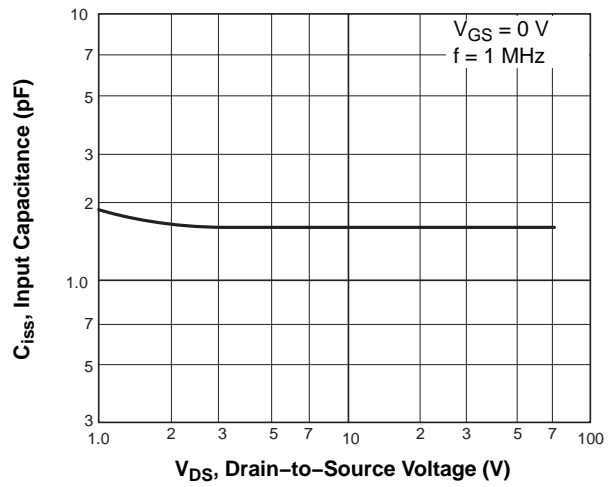


Figure 6. Input Capacitance vs. Drain-to-Source Voltage

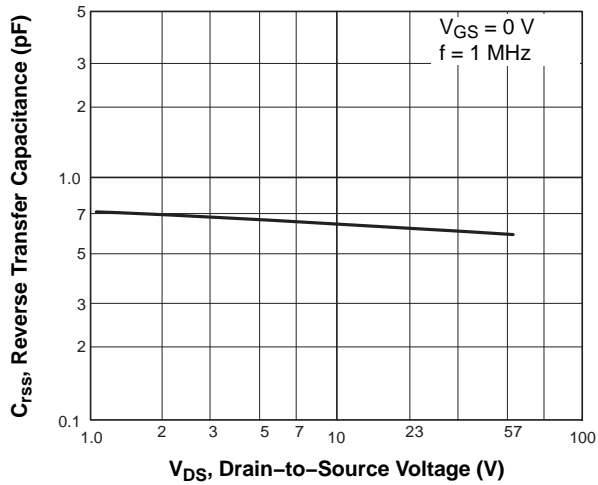
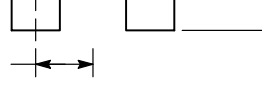


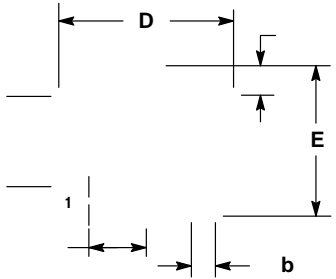
Figure 7. Reverse Transfer Capacitance vs. Drain-to-Source Voltage



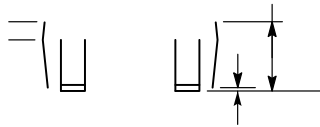
SC-59 / CP3



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MILLIMETERS		
DIM	MIN	MAX
A		



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